



DMP22D4UFO

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-20V	1.9Ω @ V _{GS} = -4.5V	-530mA
	$2.4\Omega @ V_{GS} = -2.5V$	-471mA
	3.4Ω @ V _{GS} = -1.8V	-397mA
	5.0Ω @ V _{GS} = -1.5V	-328mA

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

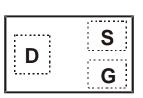
Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

X2-DFN0604-3







Features and Benefits

0.6mm x 0.4mm Package Footprint

Very Low Gate Threshold Voltage: -1.0V Max

UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

Solderable per MIL-STD-202, Method 208 3

Weight: 0.001 grams (Approximate)

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3) Qualified to AEC-Q101 Standards for High Reliability

Case Material: Molded Plastic, "Green" Molding Compound.

Terminals: Finish - Matte Tin Annealed over Copper Leadframe.

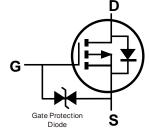
Low Package Profile

Low On-Resistance

ESD Protected Gate

Mechanical Data

Case: X2-DFN0604-3



Top View Package Pin Configuration

4P = Product Type Marking Code

Equivalent Circuit

Ordering Information (Note 4)

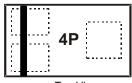
	Part Number	Case	Packaging		
	DMP22D4UFO-7B	X2-DFN0604-3	10,000/Tape & Reel		
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Top View Bar Denotes Gate and Source Side



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I _D	-530 -383	mA
Pulsed Drain Current (Note 6)			I _{DM}	-0.6	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	PD	820	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	155	°C/W
Total Power Dissipation (Note 6)	Steady State	PD	390	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	317	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	1 -						
Drain-Source Breakdown Voltage	BV _{DSS}	-20		_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		-1	μA	$V_{DS} = -16V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)			•		•	·	
Gate Threshold Voltage	V _{GS(TH)}	-0.4		-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			_	1.9		$V_{GS} = -4.5V, I_D = -100mA$	
Static Drain-Source On-Resistance	Proven	—	_	2.4	Ω	$V_{GS} = -2.5V, I_D = -50mA$	
	R _{DS(ON)}	—	—	3.4	12	$V_{GS} = -1.8V, I_D = -20mA$	
		_	—	5.0		$V_{GS} = -1.5V, I_D = -10mA$	
Diode Forward Voltage	V _{SD}	_	-0.6	-1.1	V	$V_{GS} = 0V, I_{S} = -10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	—	28.7	_	pF		
Output Capacitance	C _{oss}	_	4.2	—	pF	└ V _{DS} = -15V, V _{GS} = 0V, └ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	2.9	—	pF		
Gate Resistance	Rg	_	399	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	0.4	_	nC		
Gate-Source Charge	Q _{gs}	—	0.08		nC	− V _{GS} = -4.5V, V _{DS} =- 10V, − I _D = -250mA	
Gate-Drain Charge	Q _{gd}	—	0.06		nC		
Turn-On Delay Time	t _{D(ON)}	_	5.8	—	ns		
Turn-On Rise Time	t _R	_	5.7	—	ns	V _{DD} = -15V, V _{GS} = -4.5V,	
Turn-Off Delay Time	t _{D(OFF)}		31.1		ns	$R_{G} = 2\Omega, I_{D} = -200 mA$	
Turn-Off Fall Time	tF		16.4	—	ns	7	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided 10µs pulse duty cycle = 1%

7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.



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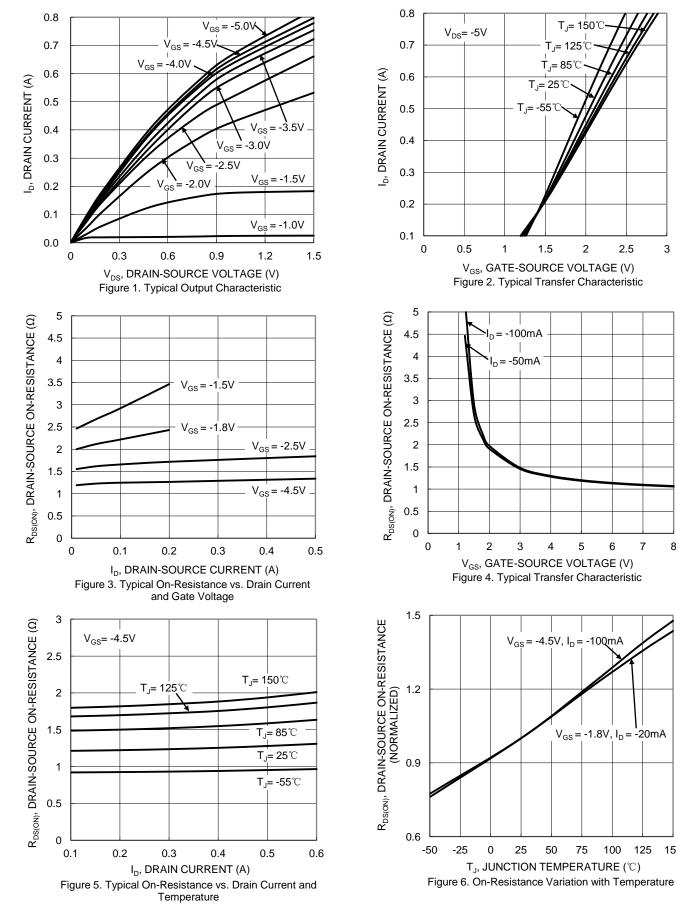
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6

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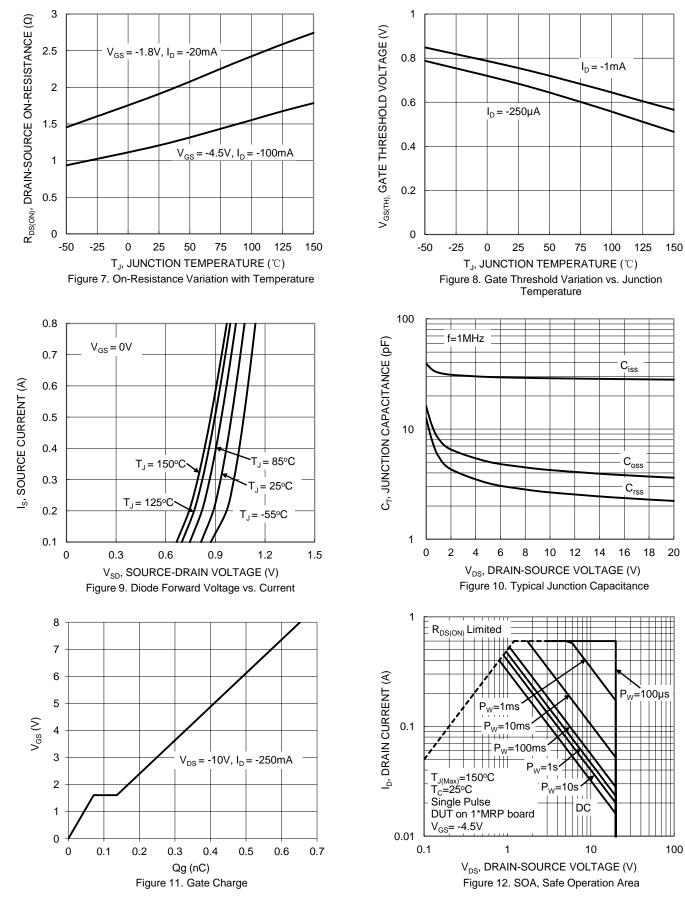


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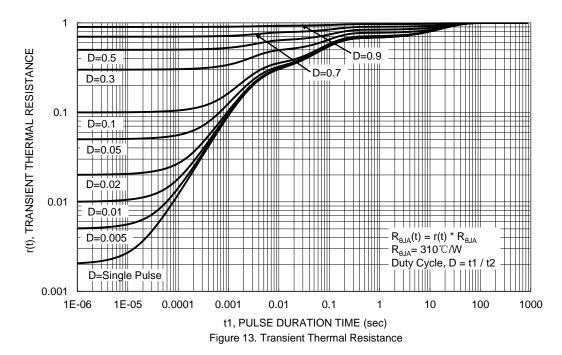
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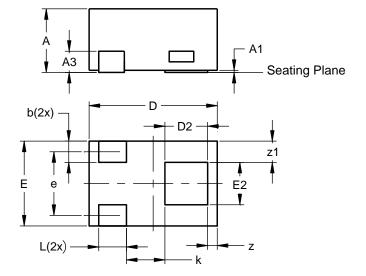




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3

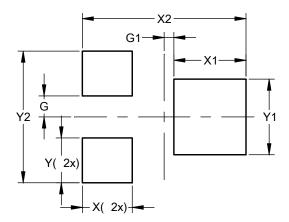


X2-DFN0604-3						
Dim	Min	Max	Тур			
Α		0.40	0.36			
A1	0.00	0.03	0.02			
A3			0.10			
b	0.07 0.15 0.		0.10			
D	0.55	0.65	0.60			
D2	0.15	0.25	0.20			
Е	0.35	0.45	0.40			
E2	0.15	0.25	0.20			
е	0.3		0.30			
k	0.15					
L	0.10	0.18	0.13			
z			0.045			
z1			0.10			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3



Dimensions	Value (in mm)
G	0.075
G1	0.035
Х	0.180
X1	0.260
X2	0.590
Y	0.160
Y1	0.270
Y2	0.470



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